

## SKiP 1513GB122-3DL

### I. Power section

Absolute maximum ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
$V_{CES}$	Operating DC link voltage	1200	V
$V_{CC}^{1)}$		900	V
$V_{GES}$		$\pm 20$	V
$I_C$		$T_s = 25 (70)^\circ\text{C}$	1500 (1125)
Inverse diode			
$I_F = -I_C$	$T_s = 25 (70)^\circ\text{C}$	1500 (1125)	A
$I_{FSM}$	$T_j = 150^\circ\text{C}$ , $t_p = 10\text{ms}$ ; sin	12960	A
$I^2t$ (Diode)	Diode, $T_j = 150^\circ\text{C}$ , 10ms	840	$\text{kA}^2\text{s}$
$T_j, (T_{stg})$		-40...+150 (125)	$^\circ\text{C}$
$V_{isol}$	rms, AC, 1min	3000	V
$I_{AC-terminal}$	per AC terminal, rms, $T_s = 70^\circ\text{C}$ , $T_{terminal} < 115^\circ\text{C}$	400	A

Characteristics $T_s = 25^\circ\text{C}$ unless otherwise specified					
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{CEsat}$	$I_C = 900\text{A}$ , $T_j = 25 (125)^\circ\text{C}$ ; measured at terminal	-	2,3 (2,5)	2,6	V
$V_{CEO}$	$T_j = 25 (125)^\circ\text{C}$ ; at terminal	-	1,1 (1,0)	1,3 (1,2)	V
$r_{CE}$	$T_j = 25 (125)^\circ\text{C}$ ; at terminal	-	1,3 (1,7)	1,5 (1,9)	$\text{m}\Omega$
$I_{CES}$	$V_{GE}=0, V_{CE}=V_{CES}, T_j=25(125)^\circ\text{C}$	-	3,6 (108)	-	mA
$E_{on} + E_{off}$	$I_C=900\text{A}$ , $V_{CC}=600\text{V}$ $T_j=125^\circ\text{C}$ $V_{CC}=900\text{V}$	-	270	-	mJ
		-	476	-	mJ
$L_{CE}$	top, bottom	-	4	-	nH
$C_{CHC}$	per phase, AC side	-	5,1	-	nF
$R_{CC-EE}$	terminal-chip, $T_j=25^\circ\text{C}$	-	0,17	-	$\text{m}\Omega$

Inverse diode					
$V_F = V_{EC}$	$I_F = 900\text{A}$ ; $T_j = 25(125)^\circ\text{C}$ measured at terminal	-	1,8 (1,5)	2,3	V
$V_{TO}$	$T_j = 25 (125)^\circ\text{C}$	-	1,0 (0,7)	1,2 (0,9)	V
$r_T$	$T_j = 25 (125)^\circ\text{C}$	-	0,9 (0,9)	1,2 (1,2)	$\text{m}\Omega$
$E_{RR}$	$I_C=900\text{A}$ $V_{CC}=600\text{V}$ $T_j=125^\circ\text{C}$ $V_{CC}=900\text{V}$	-	72	-	mJ
		-	92	-	mJ

Mechanical data					
$M_{dc}$	DC terminals, SI Units	6	-	8	Nm
$M_{ac}$	AC terminals, SI Units	13	-	15	Nm
w	SKiP <sup>®</sup> 3 System w/o heat sink	-	2,4	-	kg
w	heat sink	-	7,5	-	kg

Thermal characteristics (PX16 heat sink with fan SKF16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)

$R_{thjsIGBT}$	per IGBT	-	-	0,020	$^\circ\text{C/W}$				
$R_{thjsdiode}$	per diode	-	-	0,038	$^\circ\text{C/W}$				
$Z_{th}$	$R_i$ (mK/W) (max. values)	$\tau_i$ (s)							
		1	2	3	4				
$IGBT_{jr}$		3,4	9,6	7,0	0,0	363,0	0,18	0,04	1,0
$diode_{jr}$		12,0	12,0	18,0	20,0	30,0	5,0	0,25	0,04
$heatsink_{ra}$		2,1	20,0	5,5	1,4	210	85	11,0	0,4

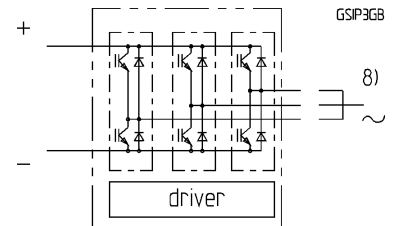
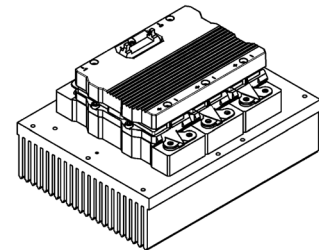
### SKiP<sup>®</sup> 3

### SK integrated intelligent Power 2-pack

### SKiP 1513GB122-3DL

Preliminary data

Case S33



### Features

- SKiP technology inside
- low loss IGBTs
- CAL diode technology
- integrated current sensor
- integrated temperature sensor
- integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiP<sup>®</sup> 3 System)
- IEC 68T.1 (climate) 40/125/56 (SKiP<sup>®</sup> 3 power section)
- UL recognized File no. E63532 (SKiP<sup>®</sup> 3 power section)

1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)

8) AC connection busbars must be connected by the user; copper busbars available on request

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## SKiiP 1513GB122-3DL

### SKiiP 3®

### SK integrated intelligent Power

## SKiiP 1513GB122-3DL

Preliminary data

#### Gate driver features

- CMOS compatible inputs
- wide range power supply
- integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- short circuit protection
- over current protection
- over voltage protection (option)
- power supply protected against under voltage
- interlock of top/bottom switch
- isolation by transformers
- fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 40/85/56 (SKiiP® 3 gate driver)

## II. Integrated gate driver

### Absolute maximum ratings

Symbol	Term	Value	Unit
V <sub>S2</sub>	unstabilized 24V power supply	35	V
V <sub>iH</sub>	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/μs
V <sub>isolIO</sub>	input / output (AC, rms, 2 s)	3000	V
V <sub>isolPD</sub>	partial discharge extinction voltage, rms, Q <sub>PD</sub> ≤ 10 pC;	1170	V
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, 2s)	1500	V
f	switching frequency	10	kHz
T <sub>op</sub> (T <sub>stg</sub> )	operating / storage temperature	- 40 ... + 85	°C

### Electrical characteristics (T<sub>a</sub> = 25 °C)

Symbol	Term	Values			Units
		min	typ	max.	
V <sub>S2</sub>	supply voltage non stabilized	13	24	30	V
I <sub>S2</sub>	V <sub>S2</sub> = 24V	$278 + 29 \cdot f / \text{kHz} + 0,00015 \cdot (I_{AC}/A)^2$			mA
V <sub>iT+</sub>	input threshold voltage (High)	11,2	–	–	V
V <sub>iT-</sub>	input threshold voltage (Low)	–	–	5,4	V
R <sub>in</sub>	input resistance	–	10	–	kΩ
C <sub>in</sub>	input capacitance	–	1	–	nF
t <sub>d(on)IO</sub>	input-output turn-on propagation time	–	1,1	–	μs
t <sub>d(off)IO</sub>	input-output turn-off propagation time	–	1,6	–	μs
t <sub>pERRRESET</sub>	error memory reset time	–	9	–	μs
t <sub>TD</sub>	top/bottom switch: interlock time	–	3,3	–	μs
I <sub>analogOUT</sub>	max. 5mA ; 8 V corresponds to 15 V supply voltage for external components; max load current	–	1500	–	A
I <sub>S1out</sub>		–	–	50	mA
I <sub>TRIPSC</sub>	over current trip level ( I <sub>analog OUT</sub> = 10V)	–	1875	–	A
T <sub>tp</sub>	over temperature protection	110	–	120	°C
U <sub>DCTRIP</sub>	U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9V) (option for GB types)	not implemented	–	–	V

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